

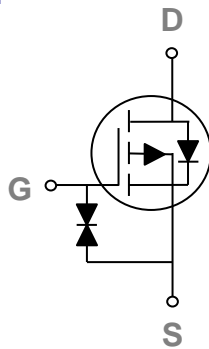
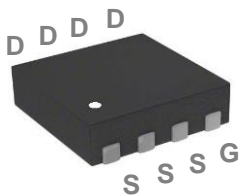
General Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
-30V	20mΩ	-30A

Features

- -30V,-30A, $R_{DS(ON)} = 20m\Omega @ V_{GS} = -10V$
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

DFN3x3 Pin Configuration

Applications

- MB / VGA / Vcore
- POL Applications
- Load Switch
- LED Application

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	-30	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	-19	A
I_{DM}	Drain Current – Pulsed ¹	-120	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	27	W
	Power Dissipation – Derate above 25°C	0.22	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	4.6	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.03	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-27V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-24V, V _{GS} =0V, T _J =125°C	---	---	-10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±20	uA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-8A	---	16	20	mΩ
		V _{GS} =-4.5V, I _D =-6A	---	26	35	mΩ
V _{GS(th)}	Gate Threshold Voltage		-1.2	-1.6	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =-250uA	---	4	---	mV/°C
gfs	Forward Transconductance	V _{DS} =-10V, I _D =-8A	---	6.8	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2, 3}		---	11	17	nC
Q _{gs}	Gate-Source Charge ^{2, 3}	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-5A	---	3.4	6	
Q _{gd}	Gate-Drain Charge ^{2, 3}		---	4.2	8	
T _{d(on)}	Turn-On Delay Time ^{2, 3}		---	5.8	11	ns
T _r	Rise Time ^{2, 3}	V _{DD} =-15V, V _{GS} =-10V, R _G =6Ω	---	18.8	36	
T _{d(off)}	Turn-Off Delay Time ^{2, 3}	I _D =-1A	---	46.9	90	
T _f	Fall Time ^{2, 3}		---	12.3	23	
C _{iss}	Input Capacitance		---	1250	2500	pF
C _{oss}	Output Capacitance	V _{DS} =-15V, V _{GS} =0V, F=1MHz	---	160	320	
C _{rss}	Reverse Transfer Capacitance		---	90	180	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-30	A
I _{SM}	Pulsed Source Current		---	---	-60	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

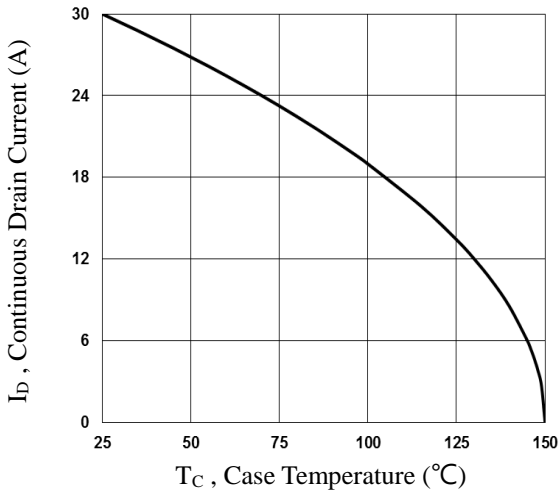


Fig.1 Continuous Drain Current vs. T_c

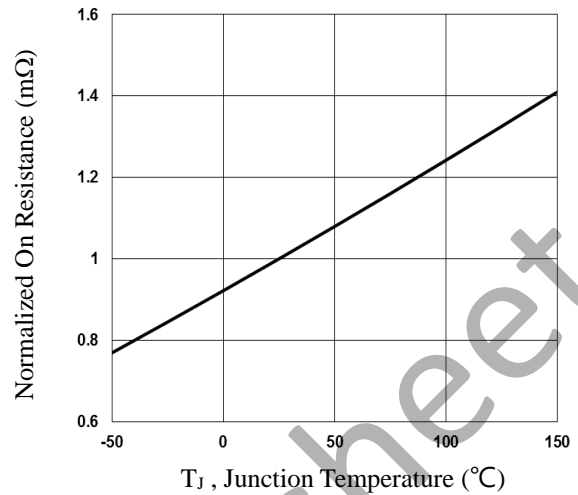


Fig.2 Normalized R_{DS(on)} vs. T_j

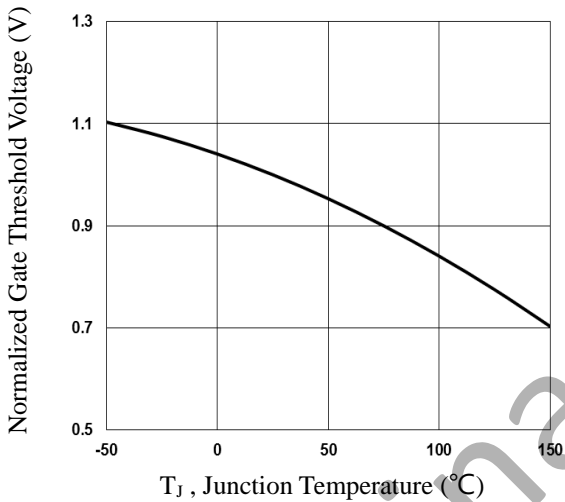


Fig.3 Normalized V_{th} vs. T_j

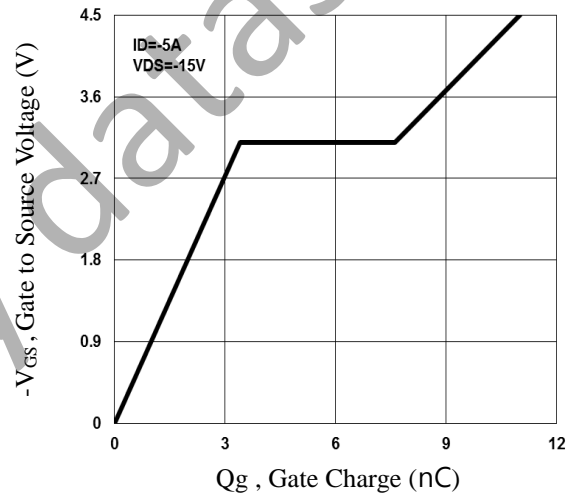


Fig.4 Gate Charge Waveform

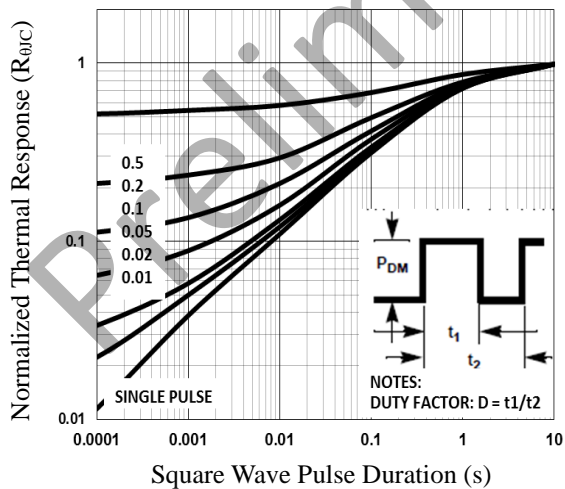


Fig.5 Normalized Transient Impedance

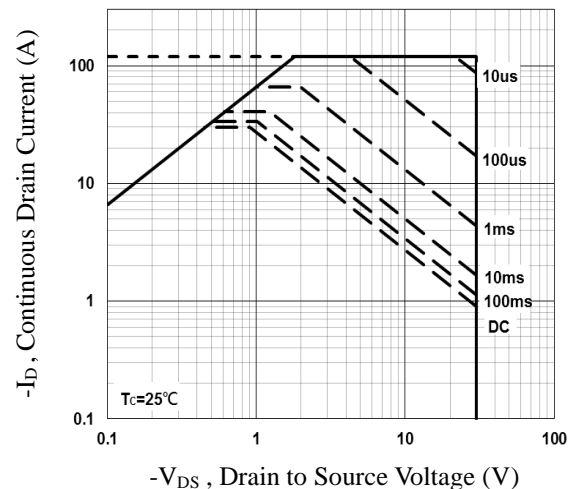


Fig.6 Maximum Safe Operation Area

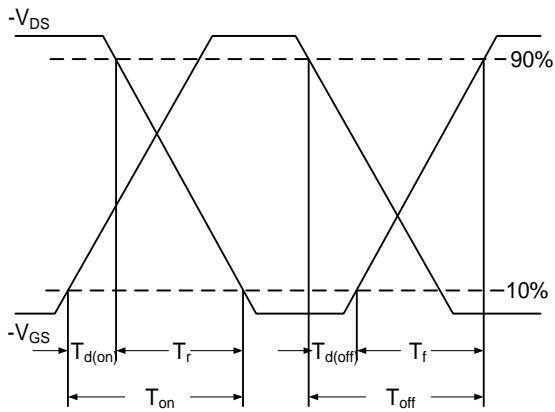


Fig.7 Switching Time Waveform

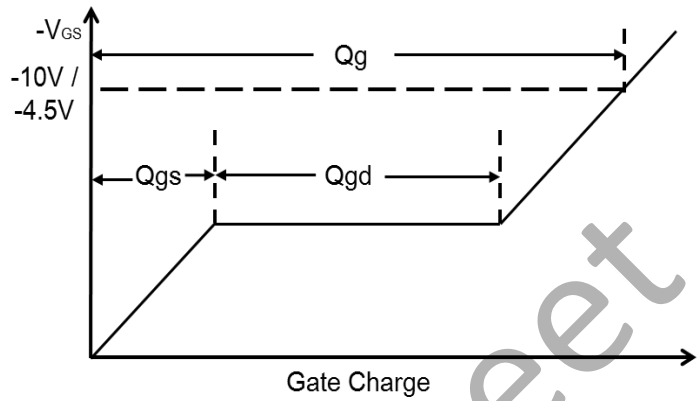
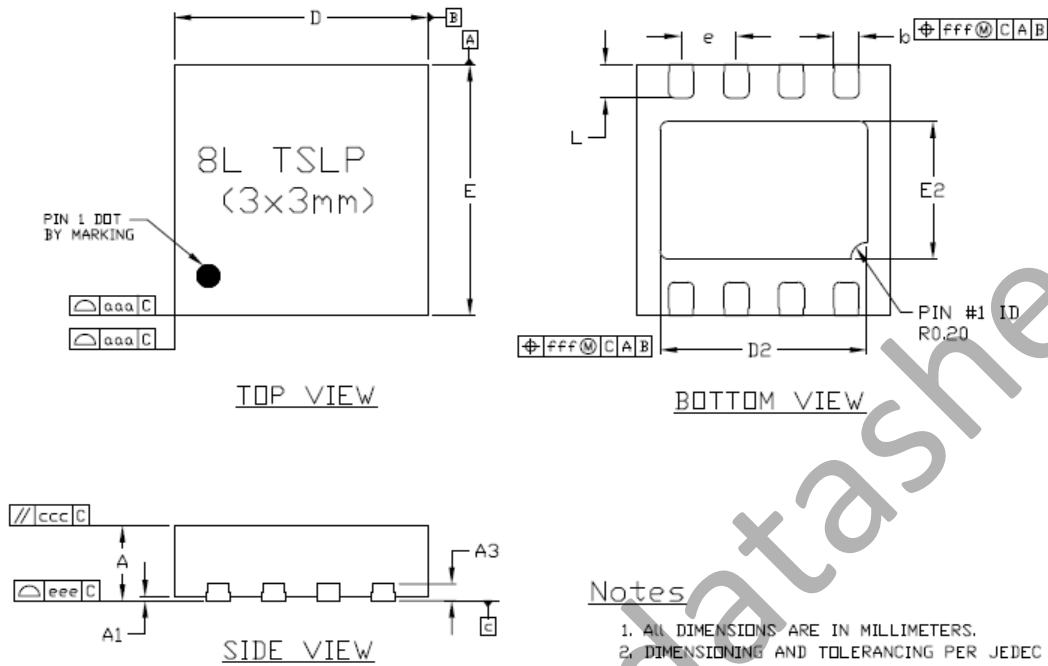


Fig.8 Gate Charge Waveform

Preliminary datasheet

DFN3x3 PACKAGE INFORMATION



Notes

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER JEDEC MO-220.

Symbol	Dimensions In Millimeters		
	Min	Nom	Max
A	0.700	0.750	0.800
A1	-	-	0.050
A3	0.203Ref.		
D	2.950	3.000	3.050
E	2.950	3.000	3.050
D2	2.400	2.450	2.500
E2	1.600	1.650	1.700
b	0.250	0.300	0.350
e	0.650BSC		
L	0.350	0.400	0.450
aaa	0.010		
bbb	0.010		
ccc	0.010		
ddd	0.050		
eee	0.080		
fff	0.100		